UNITED STATES PATENT AND TRADEMARK OFFICE

BEFORE THE PATENT TRIAL AND APPEAL BOARD

TAIWAN SEMICONDUCTOR MANUFACTURING CO., LTD, Petitioner,

V.

GODO KAISHA IP BRIDGE 1, Patent Owner.

Case IPR2017-01843¹ Patent 7,893,501

DECLARATION OF ALEXANDER D. GLEW

at 3.

IP Bridge Exhibit 2208 TSMC v. Godo Kaisha IP Bridge 1 IPR2017-01843



¹ Case IPR2017-01844 has been consolidated with this proceeding. See Paper 10

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I, Alexander D. Glew, declare:

1. I have been retained by Wolf, Greenfield & Sacks, P.C., counsel for Patent Owner Godo Kaisha IP Bridge 1 ("IP Bridge"), to submit this declaration in connection with the *Inter Partes* Review of claims 1, 4-7, 9-13, 15-19, 21, and 23-25 of U.S. Patent No. 7,893,501 ("the '501 patent"). I am being compensated for my time at a rate of \$515.00 per hour, plus actual expenses. My compensation is not dependent in any way upon the outcome of the Petition.

I. PERSONAL AND PROFESSIONAL BACKGROUND

- 2. My curriculum vitae is provided as Exhibit 2229 to this proceeding.
- 3. I earned a B.S. degree in Mechanical Engineering from the University of California, Berkeley in 1985, a M.S. degree in Mechanical Engineering from the University of California, Berkeley in 1987, a M.S. degree in Materials Science and Engineering from Stanford University in 1995, and a Ph.D. in Materials Science and Engineering from Stanford University in 2003.
- 4. I am the Founder and President of Glew Engineering Consulting, Inc., based in Mountain View, California. I have been President of Glew Engineering Consulting, Inc. since I started the company in 1997. In my role as President, I have provided consulting services to clients in the field of semiconductor manufacturing and materials, as well as to clients in other fields. I have reviewed and analyzed new semiconductor technologies and products and provided advice



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